

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IXTA2N100

• FEATURES

- Static drain-source on-resistance: $R_{DS}(on) \le 7\Omega @V_{GS}=10V$
- Fully characterized avalanche voltage and current
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATION

- DC/DC Converter
- · Switch-Mode and Resonant-Mode Power Supplies

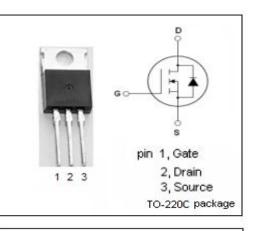
SYMBOL	PARAMETER	VALUE	UNIT			
V _{DSS}	Drain-Source Voltage	1000	V			
V _{GS}	Gate-Source Voltage	±20	V			
ID	Drain Current-Continuous	2	А			
I _{DM}	Drain Current-Single Pulsed	8	А			
PD	Total Dissipation @T _c =25°C	100	W			
Tj	Operating Junction Temperature	-55~150	°C			
T _{stg}	Storage Temperature	-55~150	°C			

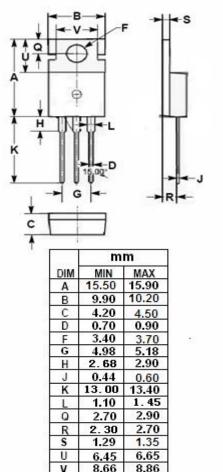
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R _{th(j-c)}	Junction-to-case thermal resistance	1.25	°C/W

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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID = 250 μ A	1000		V
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID = 250 μ A	2.0	4.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D = 1A		7	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} =0V		±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = V _{DSS} ; V _{GS} = 0V		25	μ Α
		V _{DS} = V _{DSS} ; V _{GS} = 0V;T _J = 125°C		100	
Vsd	Diode forward voltage	I _F = 2A; V _{GS} = 0V		1.5	V

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